

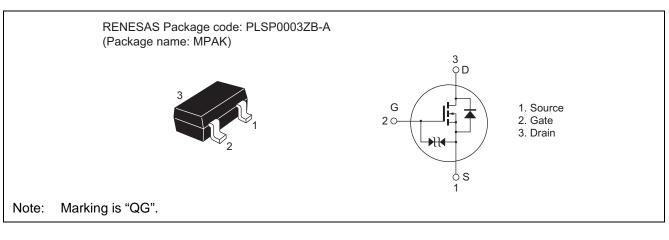
# RQK0201QGDQA

Silicon N Channel MOS FET Power Switching

# Features

- Low on-resistance
  - $R_{DS(on)} = 25 \text{ m}\Omega \text{ typ } (V_{GS} = 4.5 \text{ V}, I_D = 2.4 \text{ A})$
- Low drive current
- High speed switching
- 2.5 V gate drive

### Outline



#### **Absolute Maximum Ratings**

|  |                             |             | $(Ta = 25^{\circ}C)$ |
|--|-----------------------------|-------------|----------------------|
| ltem                                     | Symbol                      | Ratings     | Unit                 |
| Drain to source voltage                  | V <sub>DSS</sub>            | 20          | V                    |
| Gate to source voltage                   | V <sub>GSS</sub>            | ±12         | V                    |
| Drain current                            | ID                          | 4.5         | А                    |
| Drain peak current                       | I <sub>D(pulse)</sub> Note1 | 15          | А                    |
| Body - drain diode reverse drain current | I <sub>DR</sub>             | 4.5         | А                    |
| Channel dissipation                      | Pch Note2                   | 0.8         | W                    |
| Channel temperature                      | Tch                         | 150         | ۵°                   |
| Storage temperature                      | Tstg                        | -55 to +150 | ۵°                   |

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Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. When using the glass epoxy board (FR-4: 40 x 40 x 1 mm)



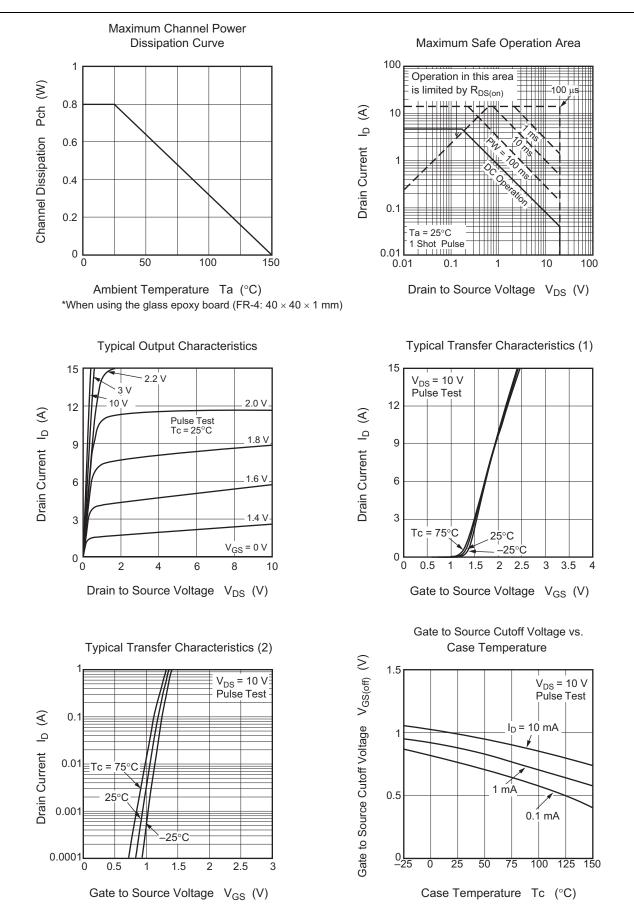
### **Electrical Characteristics**

|                                     |                      |     |      |     |      | $(Ta = 25^{\circ}C)$                        |  |
|-------------------------------------|----------------------|-----|------|-----|------|---|--|
| ltem                                | Symbol               | Min | Тур  | Max | Unit | Test conditions                             |  |
| Drain to source breakdown voltage   | V <sub>(BR)DSS</sub> | 20  | —    | —   | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$           |  |
| Gate to source breakdown voltage    | V <sub>(BR)GSS</sub> | ±12 | —    | —   | V    | $I_G = \pm 100 \ \mu A, \ V_{DS} = 0$       |  |
| Gate to source leak current         | I <sub>GSS</sub>     | _   | _    | ±10 | μA   | $V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$     |  |
| Drain to source leak current        | I <sub>DSS</sub>     | _   | _    | 1   | μA   | $V_{DS} = 20 V, V_{GS} = 0$                 |  |
| Gate to source cutoff voltage       | V <sub>GS(off)</sub> | 0.4 | _    | 1.4 | V    | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ |  |
| Drain to source on state resistance | R <sub>DS(on)</sub>  |     | 30   | 39  | mΩ   | $I_D = 2.4A, V_{GS} = 4.5 V^{Note3}$        |  |
|                                     | R <sub>DS(on)</sub>  |     | 38   | 53  | mΩ   | $I_D = 2.4A, V_{GS} = 2.5 V^{Note3}$        |  |
| Forward transfer admittance         | y <sub>fs</sub>      | 9   | 12   |     | S    | $I_D = 2.4A, V_{DS} = 10 V^{Note3}$         |  |
| Input capacitance                   | Ciss                 |     | 479  | —   | pF   | V <sub>DS</sub> = 10 V                      |  |
| Output capacitance                  | Coss                 | _   | 106  | —   | pF   | $V_{GS} = 0$                                |  |
| Reverse transfer capacitance        | Crss                 | _   | 48   | —   | pF   | f = 1 MHz                                   |  |
| Turn - on delay time                | t <sub>d(on)</sub>   | _   | 14   | —   | ns   | I <sub>D</sub> = 2.4 A                      |  |
| Rise time                           | tr                   | _   | 53   | —   | ns   | V <sub>GS</sub> = 4.5 V                     |  |
| Turn - off delay time               | t <sub>d(off)</sub>  | _   | 35   | —   | ns   | $R_L = 5.50 \Omega$                         |  |
| Fall time                           | t <sub>f</sub>       | _   | 6    | —   | ns   | Rg = 4.7 Ω                                  |  |
| Total gate charge                   | Qg                   | _   | 4.6  | —   | nC   | V <sub>DD</sub> = 10 V                      |  |
| Gate to source charge               | Qgs                  |     | 0.9  | _   | nC   | V <sub>GS</sub> = 4.5 V                     |  |
| Gate to drain charge                | Qgd                  |     | 1.3  | _   | nC   | I <sub>D</sub> = 4.5 A                      |  |
| Body - drain diode forward voltage  | V <sub>DF</sub>      | _   | 0.85 | 1.1 | V    | $I_F = 4.5 \text{ A}, V_{GS} = 0^{Note3}$   |  |

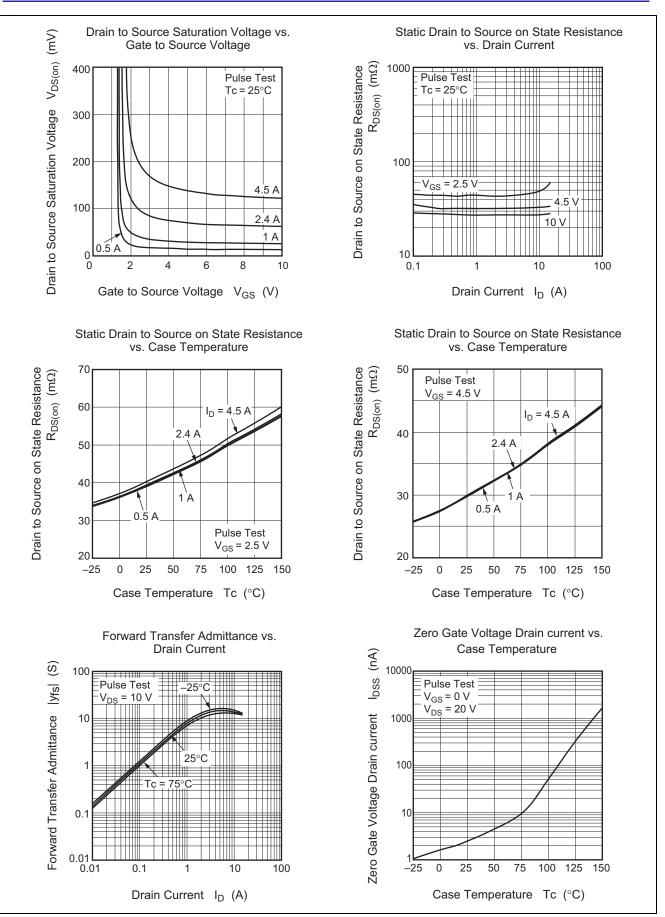
Notes: 3. Pulse test

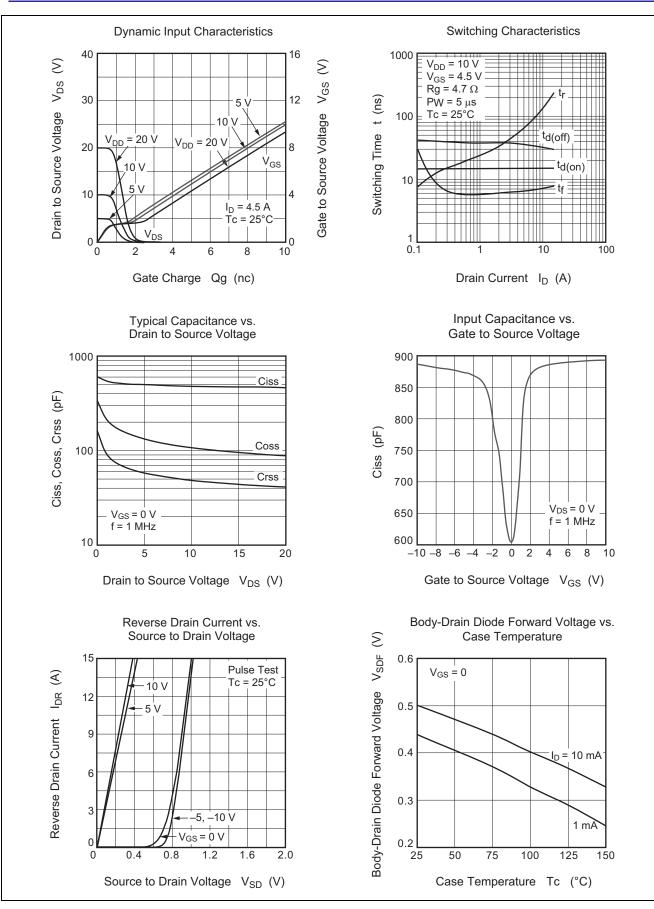


#### **Main Characteristics**



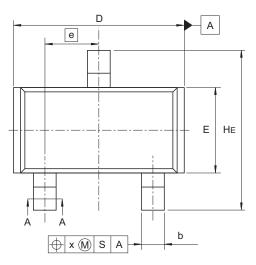


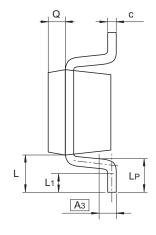


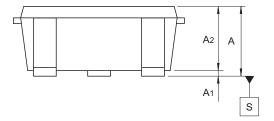


## Package Dimensions

| JEITA Package Code | RENESAS Code | Previous Code      | MASS (Typ) [g] |
|--------------------|--------------|--------------------|----------------|
| SC-59A             | PLSP0003ZB-A | MPAK(T) / MPAK(T)V | 0.011          |











| Reference      | Dimensions in millimeters |      |      |
|----------------|---------------------------|------|------|
| Symbol         | Min                       | Nom  | Max  |
| Α              | 1.0                       |      | 1.3  |
| A <sub>1</sub> | 0                         |      | 0.1  |
| A <sub>2</sub> | 1.0                       | 1.1  | 1.2  |
| A <sub>3</sub> |                           | 0.25 |      |
| b              | 0.35                      | 0.4  | 0.5  |
| С              | 0.1                       | 0.16 | 0.26 |
| D              | 2.7                       |      | 3.1  |
| E              | 1.35                      | 1.5  | 1.65 |
| е              |                           | 0.95 |      |
| HE             | 2.2                       | 2.8  | 3.0  |
| L              | 0.35                      | —    | 0.75 |
| L <sub>1</sub> | 0.15                      |      | 0.55 |
| LP             | 0.25                      |      | 0.65 |
| Х              |                           |      | 0.05 |
| Q              |                           | 0.3  |      |

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## **Ordering Information**

| Orderable Part Number | Quantity  | Shipping Container               |
|-----------------------|-----------|----------------------------------|
| RQK0201QGDQATL-H      | 3000 pcs. | φ178 mm reel, 8 mm Emboss taping |



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